

**AMENDMENTS TO THE SPECIFICATION**

On page 12 of the specification, please amend paragraph [0058] as follows:

[0058] The invention is not limited to the structure of the gates 306 and 307 described above. Additional layers may be added or the gates 306 and 307 may be altered as is desired and known in the art. For example, a silicide layer (not shown) may be formed between the gate electrodes 340b and the second insulating layers 340c. The silicide layer may be included in the gates 306 and 307, or in all of the transistor gate structures in an image sensor circuit, and may be titanium silicide, tungsten silicide, cobalt silicide, molybdenum silicide, or tantalum silicide. This additional conductive layer may also be a barrier layer/~~refractor~~refractory metal, such as TiN/W or W/N<sub>x</sub>/W, or it could be formed entirely of WN<sub>x</sub>.